



NPN SILICON RF TRANSISTOR NE85634 / 2SC3357

NPN EPITAXIAL SILICON RF TRANSISTOR FOR HIGH-FREQUENCY LOW-NOISE AMPLIFICATION 3-PIN POWER MINIMOLD

FEATURES

- Low noise and high gain
 - ★ NF = 1.1 dB TYP., $G_a = 7.5$ dB TYP. @ $V_{CE} = 10$ V, $I_c = 7$ mA, $f = 1$ GHz
 - NF = 1.8 dB TYP., $G_a = 9.0$ dB TYP. @ $V_{CE} = 10$ V, $I_c = 40$ mA, $f = 1$ GHz
- ★ • High power gain : MAG = 10 dB TYP. @ $I_c = 40$ mA, $f = 1$ GHz
- Large P_{tot} : $P_{tot} = 1.2$ W (Mounted on $16\text{ cm}^2 \times 0.7$ mm (t) ceramic substrate)
- Small package : 3-pin power minimold package

★ ORDERING INFORMATION

Part Number	Quantity	Supplying Form
NE85634-A 2SC3357-A	25 pcs (Non reel) (Pb-Free)	• 12 mm wide embossed taping
NE85634-T1-A 2SC3357-T1-A	1 kpcs/reel (Pb-Free)	• Collector face the perforation side of the tape

Remark To order evaluation samples, contact your nearby sales office.
The unit sample quantity is 25 pcs.

ABSOLUTE MAXIMUM RATINGS ($T_A = +25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO}	20	V
Collector to Emitter Voltage	V_{CEO}	12	V
Emitter to Base Voltage	V_{EBO}	3.0	V
Collector Current	I_c	100	mA
Total Power Dissipation	P_{tot} ^{Note}	1.2	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +150	$^\circ\text{C}$

Note Mounted on $16\text{ cm}^2 \times 0.7$ mm (t) ceramic substrate

Caution: Observe precautions when handling because these devices are sensitive to electrostatic discharge

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

THERMAL RESISTANCE

Parameter	Symbol	Value	Unit
Junction to Ambient Resistance	$R_{th(j-a)}$ Note	62.5	°C/W

Note Mounted on 16 cm² × 0.7 mm (t) ceramic substrate

ELECTRICAL CHARACTERISTICS (T_A = +25°C)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
DC Characteristics						
Collector Cut-off Current	I _{CBO}	V _{CB} = 10 V, I _E = 0 mA	–	–	1.0	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 1.0 V, I _C = 0 mA	–	–	1.0	μA
DC Current Gain	h _{FE} Note 1	V _{CE} = 10 V, I _C = 20 mA	50	120	250	–
RF Characteristics						
Gain Bandwidth Product	f _T	V _{CE} = 10 V, I _C = 20 mA	–	6.5	–	GHz
Insertion Power Gain	S _{21e} ²	V _{CE} = 10 V, I _C = 20 mA, f = 1 GHz	–	9.0	–	dB
Noise Figure (1)	NF	V _{CE} = 10 V, I _C = 7 mA, f = 1 GHz	–	1.1	–	dB
Noise Figure (2)	NF	V _{CE} = 10 V, I _C = 40 mA, f = 1 GHz	–	1.8	3.0	dB
Reverse Transfer Capacitance	C _{re} Note 2	V _{CB} = 10 V, I _E = 0 mA, f = 1 MHz	–	0.65	1.0	pF

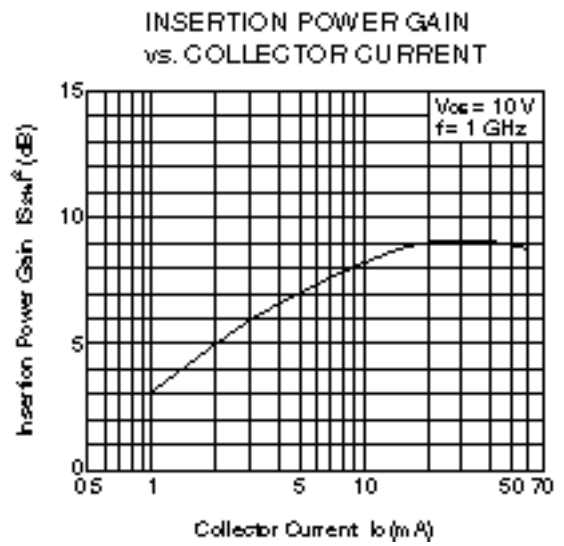
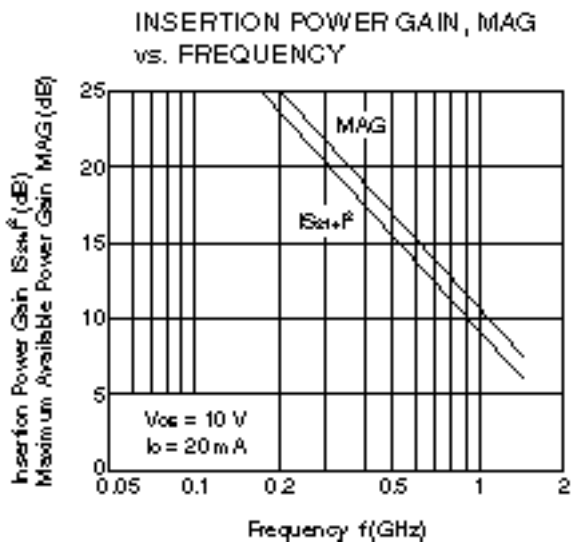
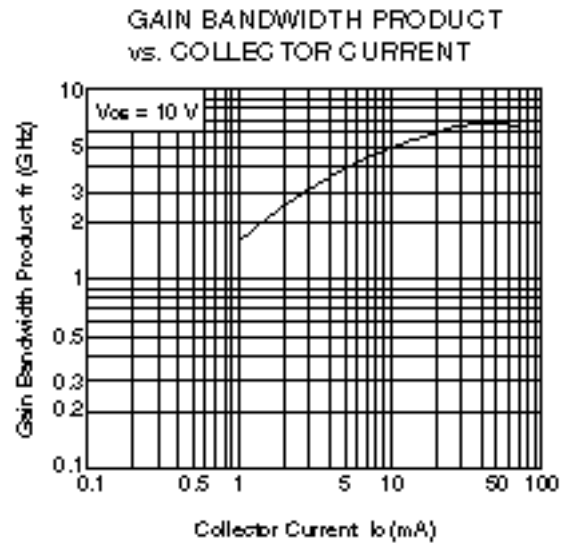
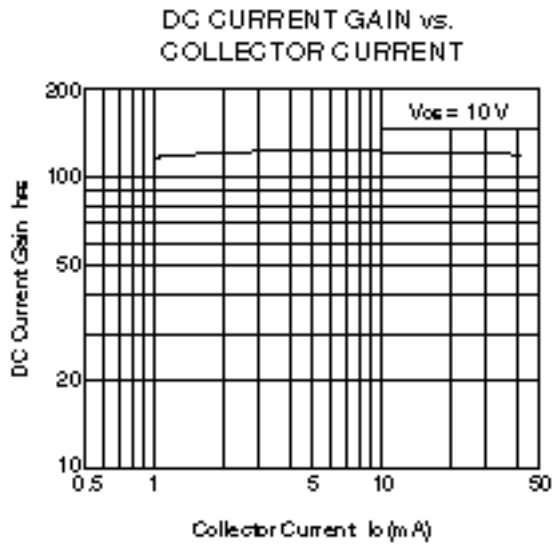
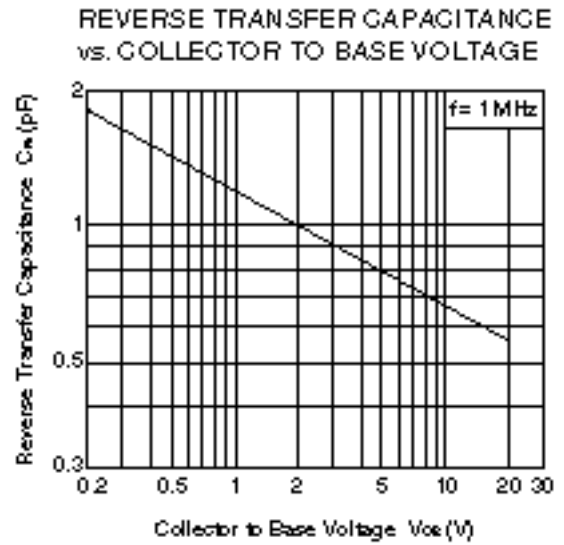
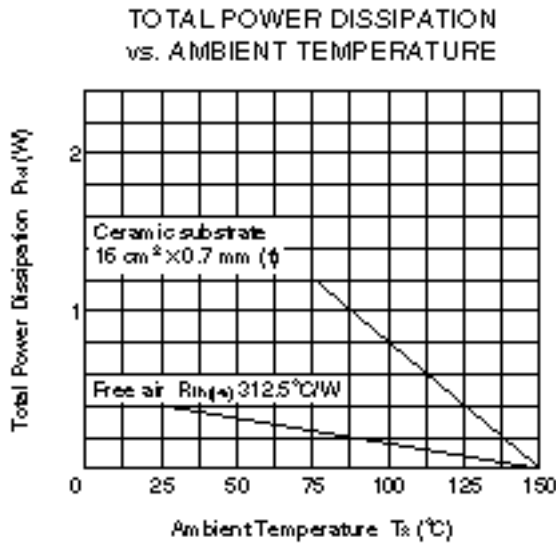
Notes 1. Pulse measurement: PW ≤ 350 μs, Duty Cycle ≤ 2%

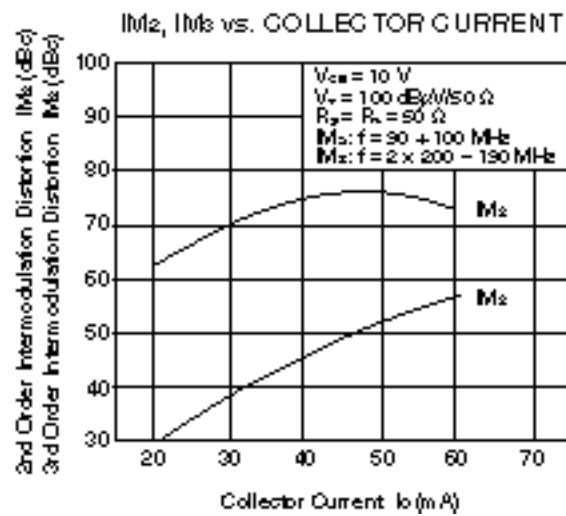
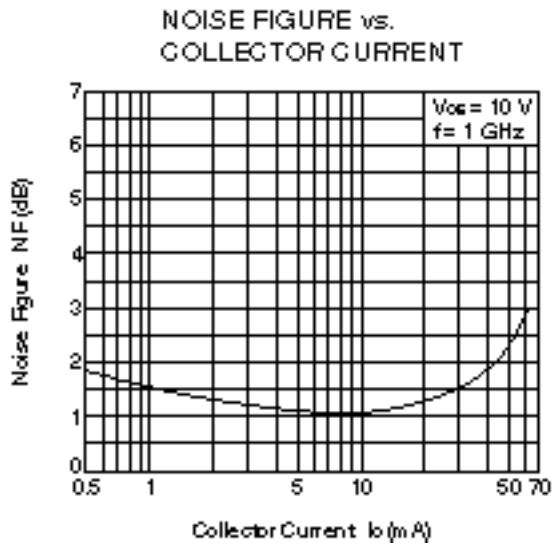
2. The emitter terminal and the case shall be connected to the guard terminal of the three-terminal capacitance bridge.

h_{FE} CLASSIFICATION

Rank	RH	RF	RE
Marking	RH	RF	RE
h _{FE} Value	50 to 100	80 to 160	125 to 250

• TYPICAL CHARACTERISTICS (T_A = +25°C, unless otherwise specified)





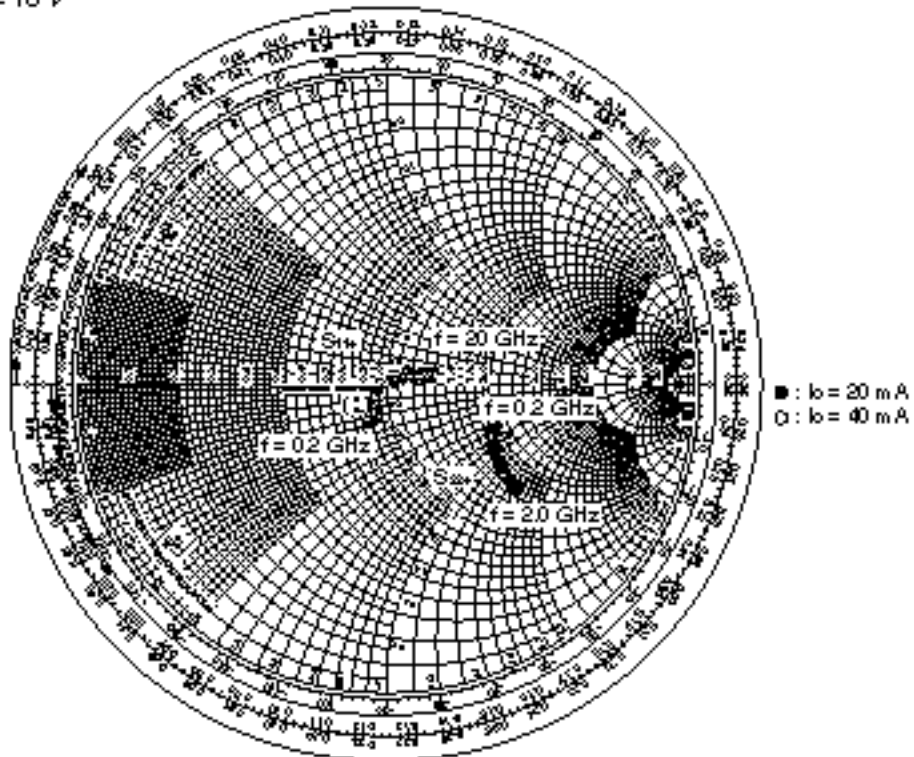
Remark The graphs indicate nominal characteristics.

S-PARAMETERS

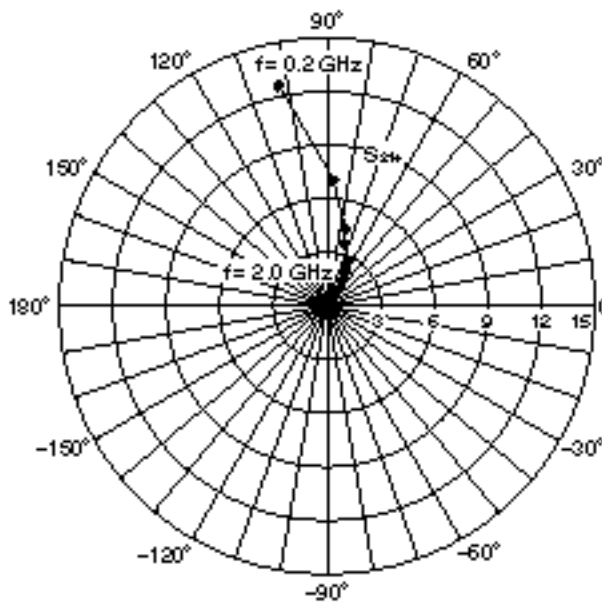
- S-parameters and noise parameters are provided on our Web site in a format (S2P) that enables the direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.
- Click here to download S-parameters.
- [RF and Microwave] @ [Device Parameters]
- URL <http://www.necel.com/microwave/en/>

SMITH CHART

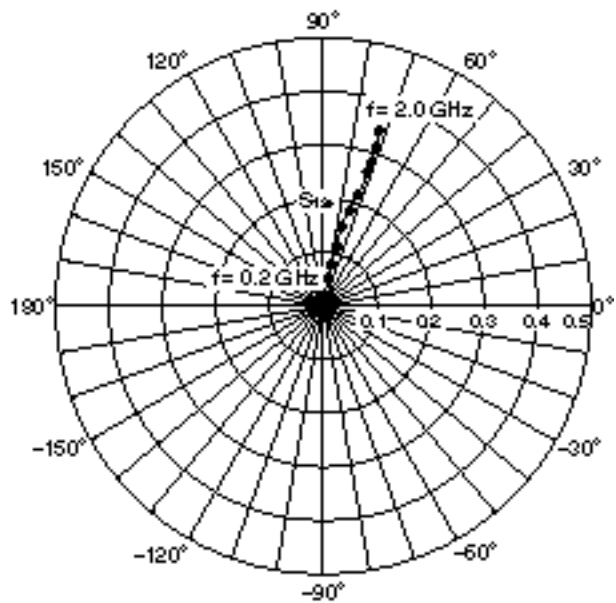
S_{11} , S_{22} -FREQUENCY
 CONDITION : $V_{CE} = 10\text{ V}$



S_{21} -FREQUENCY
 CONDITION : $V_{CE} = 10\text{ V}$, $I_b = 20\text{ mA}$

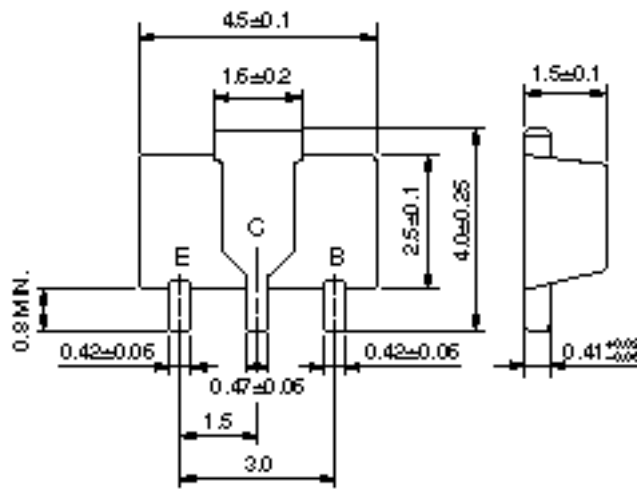


S_{12} -FREQUENCY
 CONDITION : $V_{CE} = 10\text{ V}$, $I_b = 20\text{ mA}$



PACKAGE DIMENSIONS

3-PIN POWER MINIMOLD (UNIT: mm)



PIN CONNECTIONS

- E : Emitter
- : Collector (Fin)
- B : Base

(IEC : SOT-89)

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

CEL:

[NE85634-T1-A](#)